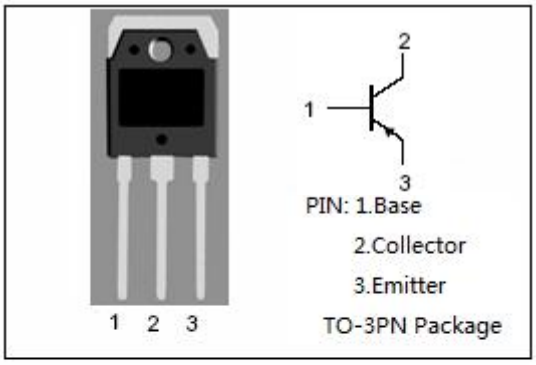
isc Silicon PNP Power Transistor 2SA1988

DESCRIPTION

- High Voltage
- TO-3P package
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

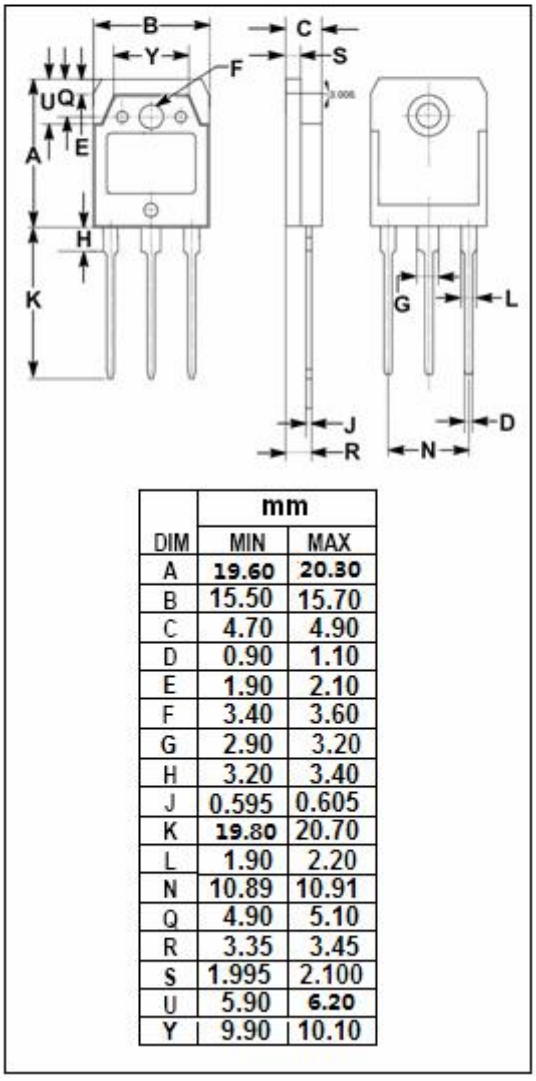


APPLICATIONS

- The 2SA1988 is PNP silicon power transistor that designed for audio frequency power amplifier

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
P_C	Collector Power Dissipation @T_a=25℃	20	W
	Collector Power Dissipation @T_C=25℃	100	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc Silicon PNP Power Transistor 2SA1988

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-200			V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -500mA ; V_{CE}= -5V			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -200V ; I_E=0			-50	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3V; I_C=0			-50	μA
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -5V	70		200	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1MHz		270		pF
f_T	Current-Gain—Bandwidth Product	I_C= -1mA ; V_{CE}= -5V		40		MHz